

TOSHIBA Field Effect Transistor Silicon N Channel MOS Type ( $\pi$ -MOSV)

## 2SK3131

### Chopper Regulator DC-DC Converter and Motor Drive Applications

- Fast reverse recovery time :  $t_{rr} = 105 \text{ ns (typ.)}$
- Built-in high-speed free-wheeling diode
- Low drain-source ON resistance :  $R_{DS(ON)} = 0.085 \Omega \text{ (typ.)}$
- High forward transfer admittance :  $|Y_{fs}| = 35 \text{ S (typ.)}$
- Low leakage current :  $I_{DSS} = 100 \mu\text{A (max)} \text{ (} V_{DS} = 500 \text{ V)}$
- Enhancement-mode :  $V_{th} = 2.4 \sim 3.4 \text{ V (} V_{DS} = 10 \text{ V, } I_D = 1 \text{ mA)}$

### Maximum Ratings ( $T_a = 25^\circ\text{C}$ )

Characteristics	Symbol	Rating	Unit
Drain-source voltage	$V_{DSS}$	500	V
Drain-gate voltage ( $R_{GS} = 20 \text{ k}\Omega$ )	$V_{DGR}$	500	V
Gate-source voltage	$V_{GSS}$	$\pm 30$	V
DC Drain current	DC (Note 1)	$I_D$	50 A
	Pulse (Note 1)	$I_{DP}$	200 A
Drain power dissipation ( $T_c = 25^\circ\text{C}$ )	$P_D$	250	W
Single pulse avalanche energy (Note 2)	$E_{AS}$	525	mJ
Avalanche current	$I_{AR}$	50	A
Repetitive avalanche energy (Note 3)	$E_{AR}$	25	mJ
Channel temperature	$T_{ch}$	150	$^\circ\text{C}$
Storage temperature range	$T_{stg}$	$-55 \sim 150$	$^\circ\text{C}$

### Thermal Characteristics

Characteristics	Symbol	Max	Unit
Thermal resistance, channel to case	$R_{th(ch-c)}$	0.5	$^\circ\text{C/W}$
Thermal resistance, channel to ambient	$R_{th(ch-a)}$	35.7	$^\circ\text{C/W}$

Note 1: Please use devices on condition that the channel temperature is below  $150^\circ\text{C}$ .

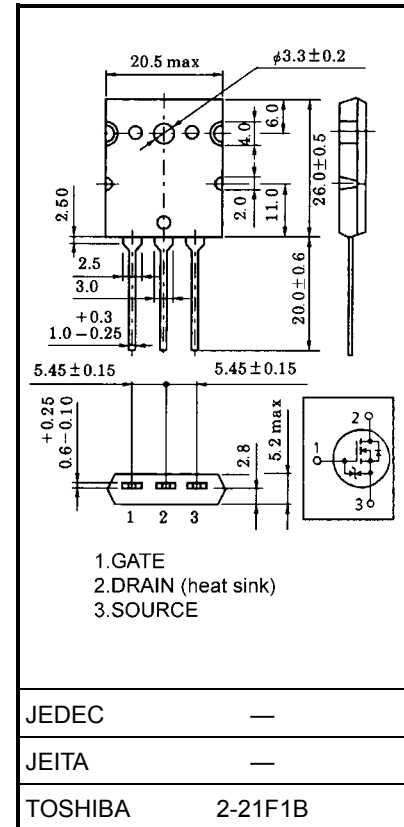
Note 2:  $V_{DD} = 90 \text{ V}$ ,  $T_{ch} = 25^\circ\text{C}$  (initial),  $L = 357 \mu\text{H}$ ,  $R_G = 25 \Omega$ ,  $I_{AR} = 50 \text{ A}$

Note 3: Repetitive rating; Pulse width limited by maximum channel temperature.

This transistor is an electrostatic sensitive device.

Please handle with caution.

Unit: mm



Weight: 9.75 g (typ.)

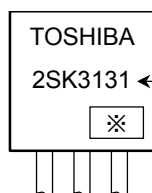
## Electrical Characteristics (Ta = 25°C)

Characteristics		Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current		$I_{GSS}$	$V_{GS} = \pm 25\text{ V}, V_{DS} = 0\text{ V}$	—	—	$\pm 10$	$\mu\text{A}$
Gate-source breakdown voltage		$V_{(BR)GSS}$	$I_G = \pm 100\ \mu\text{A}, V_{DS} = 0\text{ V}$	$\pm 30$	—	—	V
Drain cut-off current		$I_{DSS}$	$V_{DS} = 500\text{ V}, V_{GS} = 0\text{ V}$	—	—	100	$\mu\text{A}$
Drain-source breakdown voltage		$V_{(BR)DSS}$	$I_D = 10\text{ mA}, V_{GS} = 0\text{ V}$	500	—	—	V
Gate threshold voltage		$V_{th}$	$V_{DS} = 10\text{ V}, I_D = 1\text{ mA}$	2.4	—	3.4	V
Drain-source ON resistance		$R_{DS(ON)}$	$V_{GS} = 10\text{ V}, I_D = 25\text{ A}$	—	0.085	0.11	$\Omega$
Forward transfer admittance		$ Y_{fs} $	$V_{DS} = 10\text{ V}, I_D = 25\text{ A}$	15	35	—	S
Input capacitance		$C_{iss}$	$V_{DS} = 10\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$	—	11000	—	pF
Reverse transfer capacitance		$C_{rss}$		—	2100	—	
Output capacitance		$C_{oss}$		—	4200	—	
Switching time	Rise time	$t_r$		—	105	—	ns
	Turn-on time	$t_{on}$		—	160	—	
	Fall time	$t_f$		—	65	—	
	Turn-off time	$t_{off}$		Duty $\leq 1\%$ , $t_w = 10\ \mu\text{s}$	—	245	
Total gate charge (Gate-source plus gate-drain)		$Q_g$	$V_{DD} \approx 400\text{ V}, V_{GS} = 10\text{ V}, I_D = 50\text{ A}$	—	280	—	nC
Gate-source charge		$Q_{gs}$		—	150	—	
Gate-drain ("miller") charge		$Q_{gd}$		—	130	—	

## Source-Drain Ratings and Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Continuous drain reverse current (Note 1)	$I_{DR}$	—	—	—	50	A
Pulse drain reverse current (Note 1)	$I_{DRP}$	—	—	—	200	A
Forward voltage (diode)	$V_{DSF}$	$V_{DR} = 25\text{ A}, V_{GS} = 0\text{ V}$	—	—	-1.7	V
Reverse recovery time	$t_{rr}$	$I_{DR} = 50\text{ A}, V_{GS} = 0\text{ V}$	—	105	—	ns
Reverse recovery charge	$Q_{rr}$	$di_{DR} / dt = 100\text{ A} / \mu\text{s}$	—	380	—	nC

## Marking

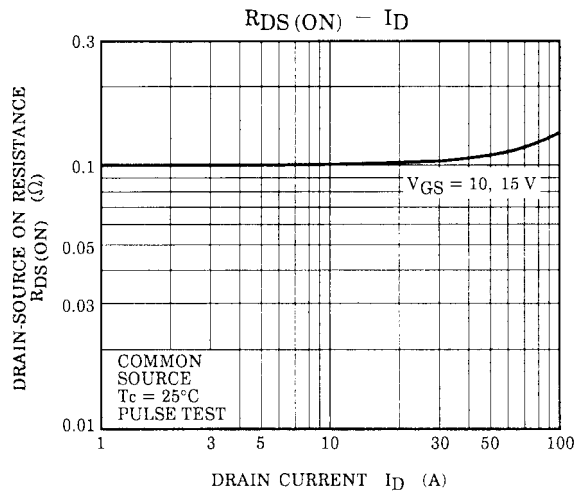
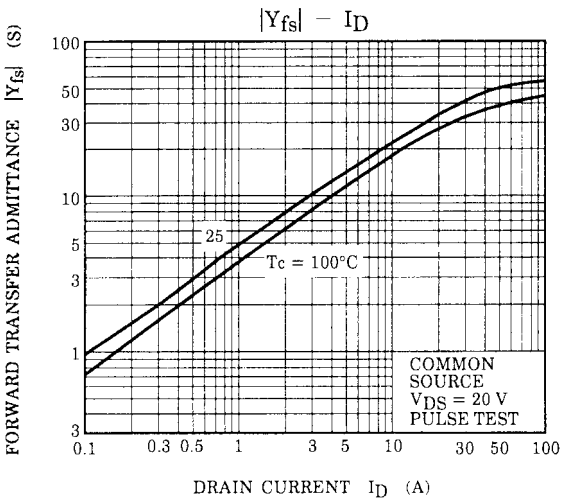
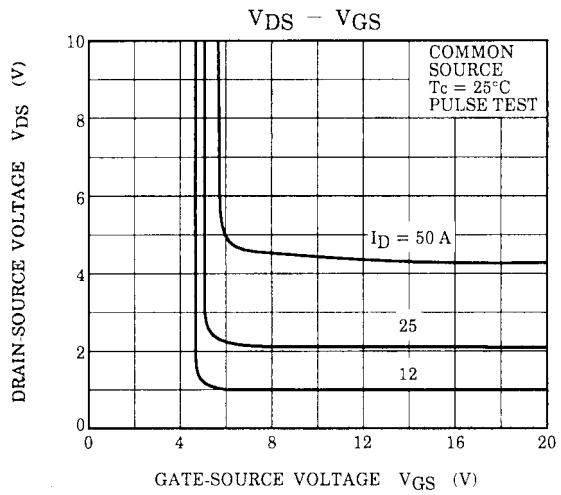
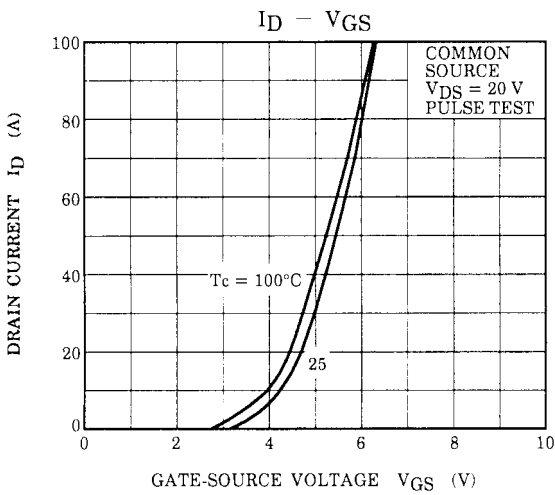
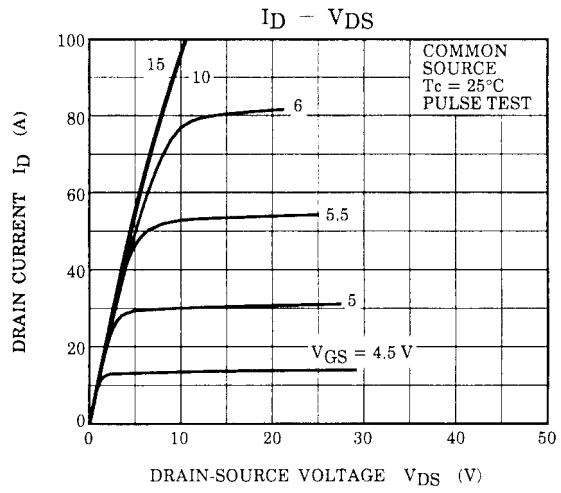
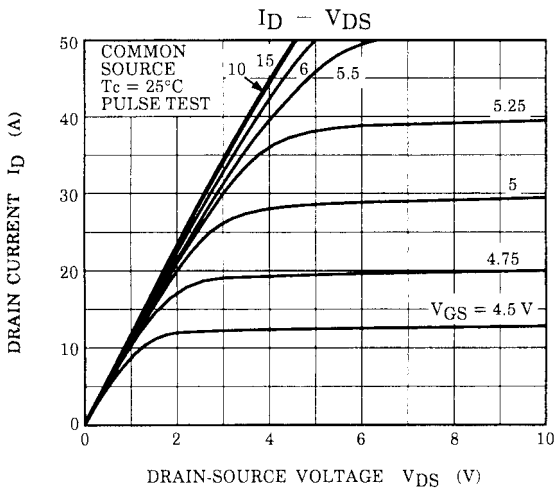


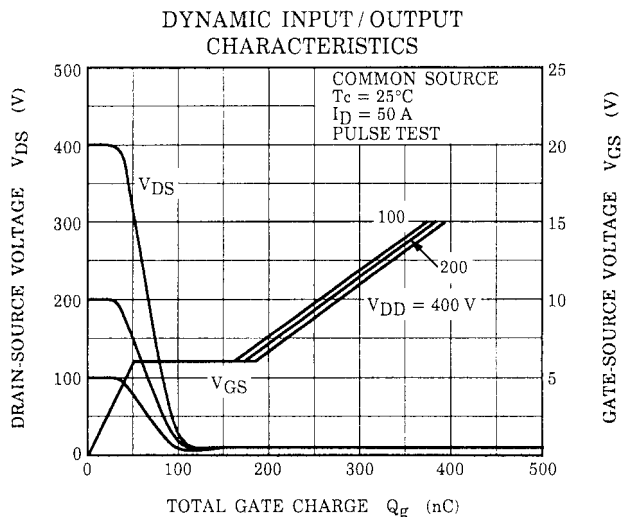
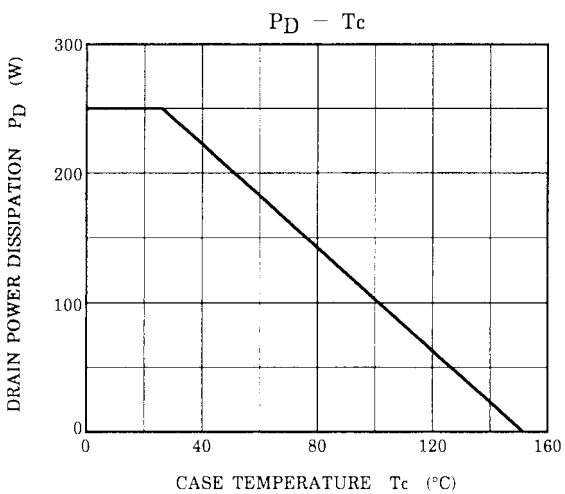
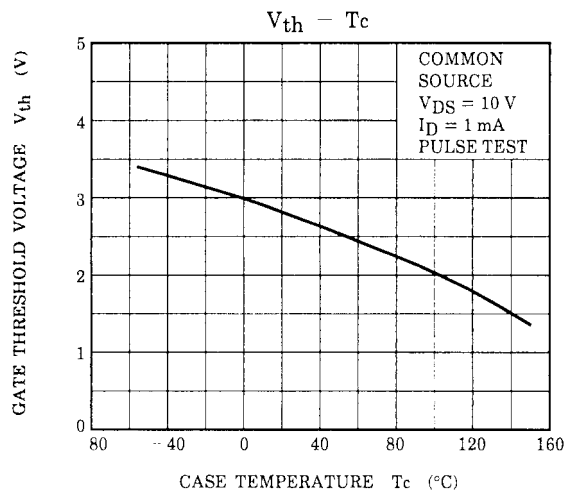
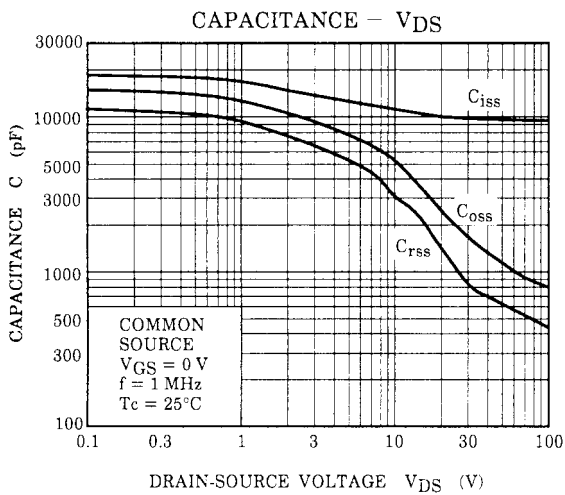
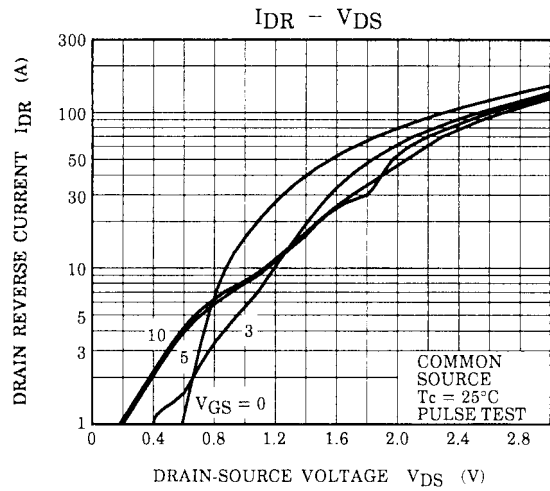
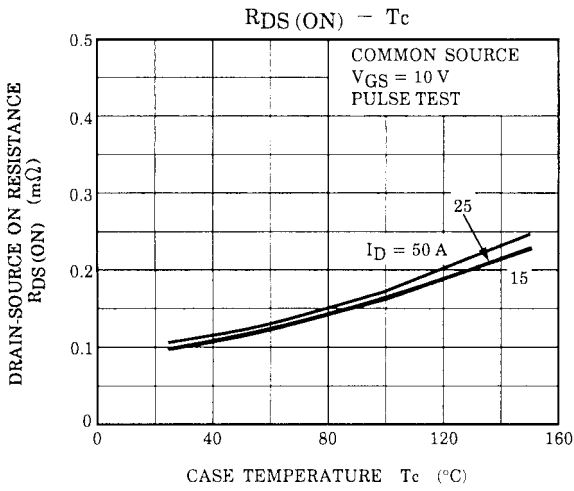
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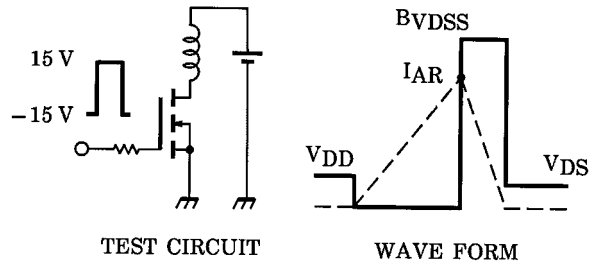
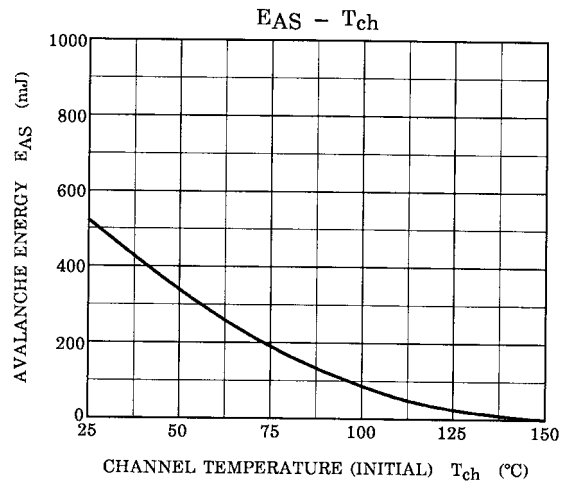
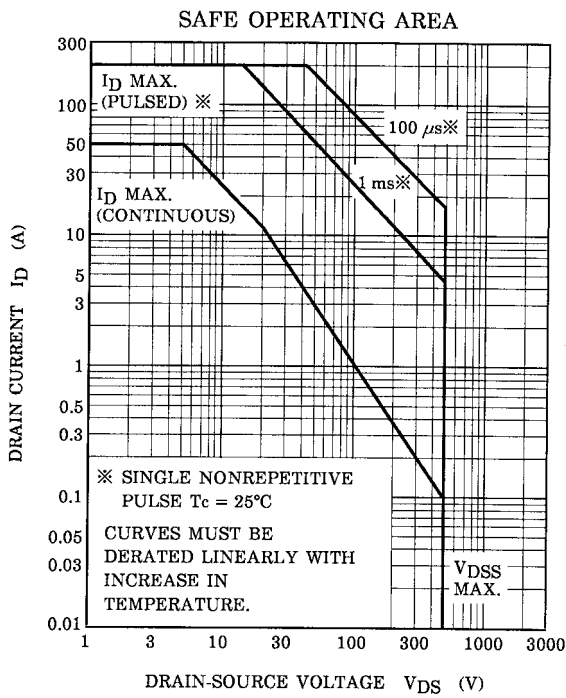
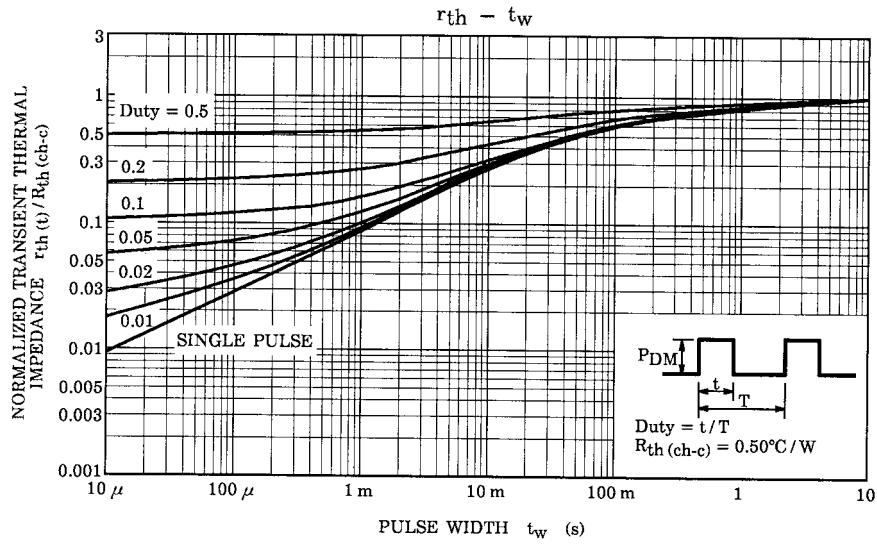
※ Lot Number

□ □ — Month (starting from alphabet A)

□ — Year (last number of the christian era)







$R_G = 25 \Omega$   
 $V_{DD} = 90 V, L = 357 \mu H$

$$E_{AS} = \frac{1}{2} \cdot L \cdot I^2 \cdot \left( \frac{BVDSS}{BVDSS - V_{DD}} \right)$$

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